ABSTRACT OF THE DISCLOSURE

A method of forming a reaction product includes providing a semiconductor substrate comprising a first material. A second material is formed over the first material. The first and second materials are of different compositions, and are proximate one another at an interface. The first and second materials as being proximate one another at the interface are capable of reacting with one another at some minimum reaction temperature when in an inert non-plasma atmosphere at a pressure. The interface is provided at a processing temperature which is at least 50°C below the minimum reaction temperature, and is provided at the pressure. With the interface at the processing temperature and at the pressure, the substrate is exposed to a plasma effective to impart a reaction of the first material with the second material to form a reaction product third material of the first and second materials over the first material. Other aspects and implementations are contemplated.